

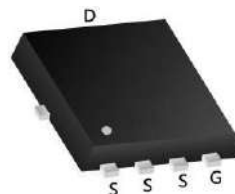
N-Ch 100V Fast Switching MOSFETs

Features:

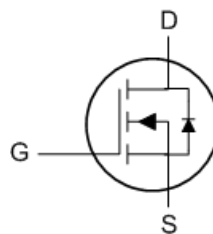
- ★ Advanced Trench MOS Technology
- ★ 100% EAS Guaranteed
- ★ Fast Switching Speed
- ★ Green Device Available

Applications:

- ★ High Frequency Switching and Synchronous Rectification.
- ★ DC/DC Converter.



PRPAK5X6 Pin Configuration



Product Summary

BVDSS	RDS(on)	ID
100V	11.5mΩ	60A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current ¹	60	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current ¹	39	A
I_{DM}	Pulsed Drain Current ²	160	A
EAS	Single Pulse Avalanche Energy ³	33	mJ
I_{AS}	Avalanche Current	15	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	56.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	2.2	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	8	11.5	mΩ
	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =10A	---	11.6	15	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	---	2.4	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
Q _g	Total Gate Charge (10V)	V _{DS} =50V, V _{GS} =10V, I _D =20A	---	29	---	nC
Q _g	Total Gate Charge (4.5V)		---	14	---	
Q _{gs}	Gate-Source Charge		---	6.5	---	
Q _{gd}	Gate-Drain Charge		---	5.5	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω, I _D =20A	---	8	---	ns
T _r	Rise Time		---	4	---	
T _{d(off)}	Turn-Off Delay Time		---	28	---	
T _f	Fall Time		---	6	---	
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	2550	---	pF
C _{oss}	Output Capacitance		---	305	---	
C _{rss}	Reverse Transfer Capacitance		---	12	---	

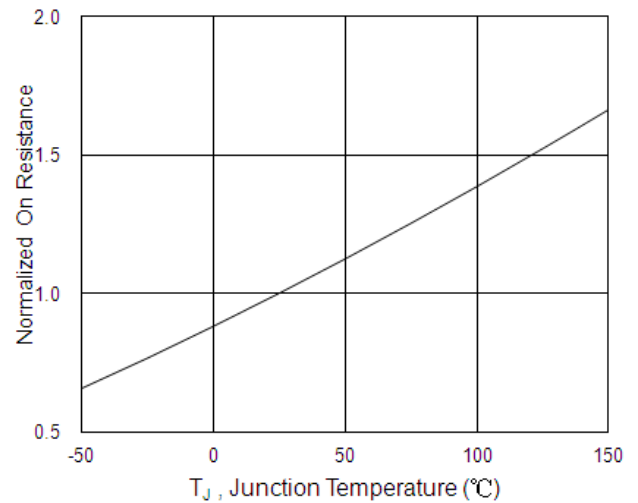
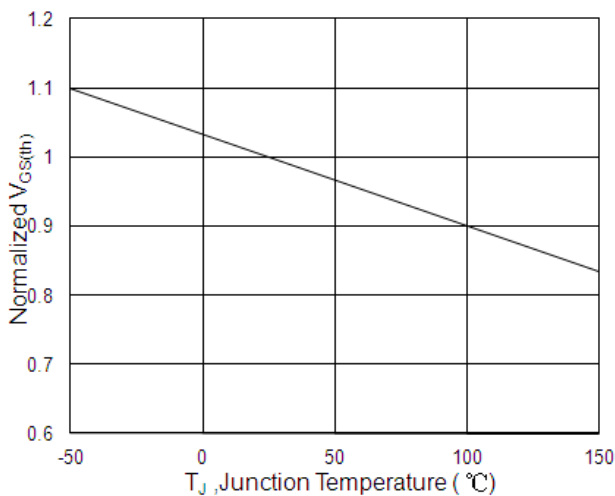
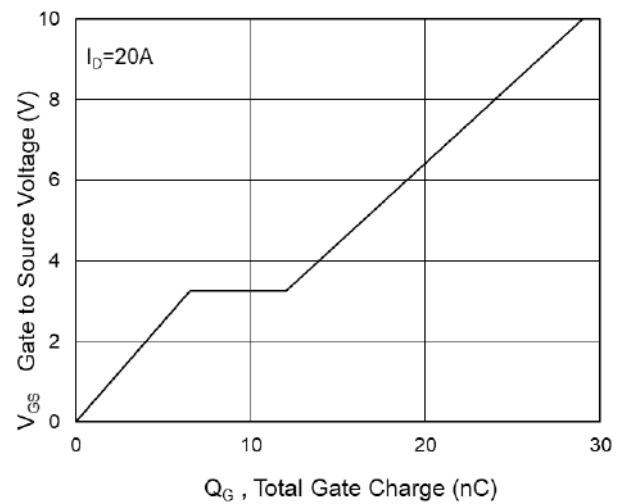
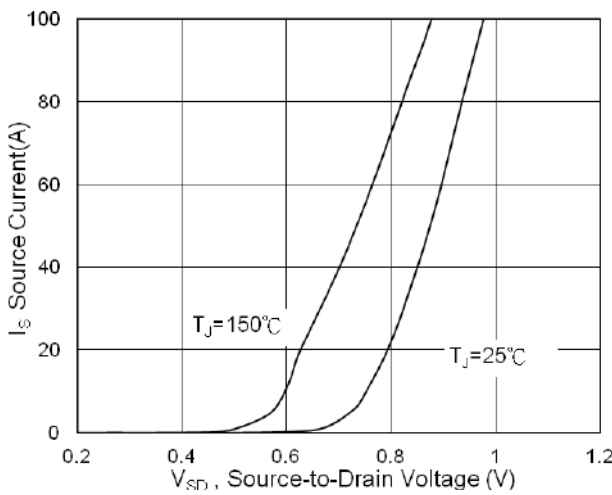
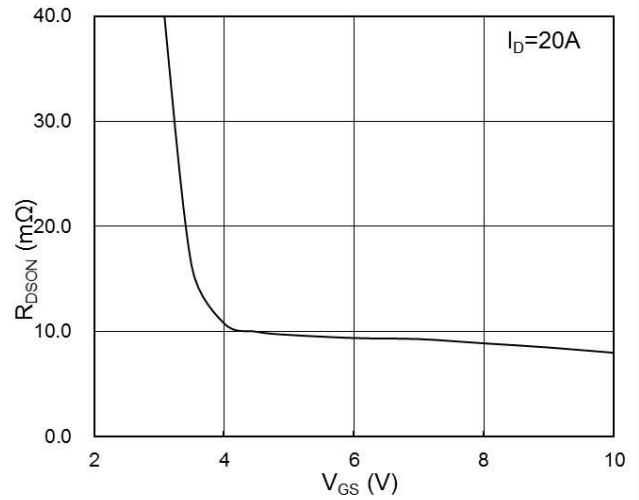
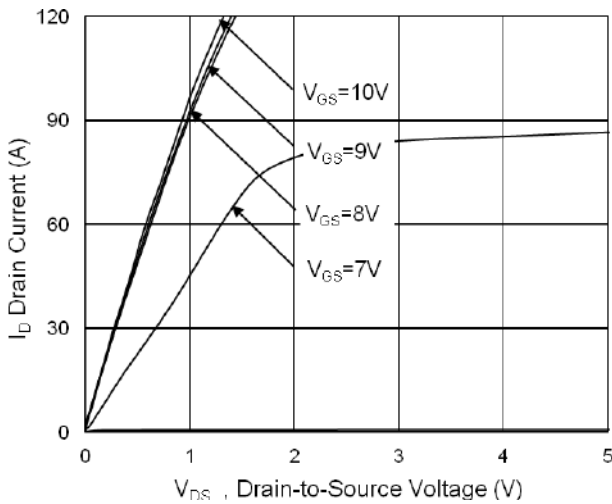
Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	35	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A, di/dt=100A/μs, T _J =25°C	---	45	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	165	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.3mH, I_{AS}=15A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics



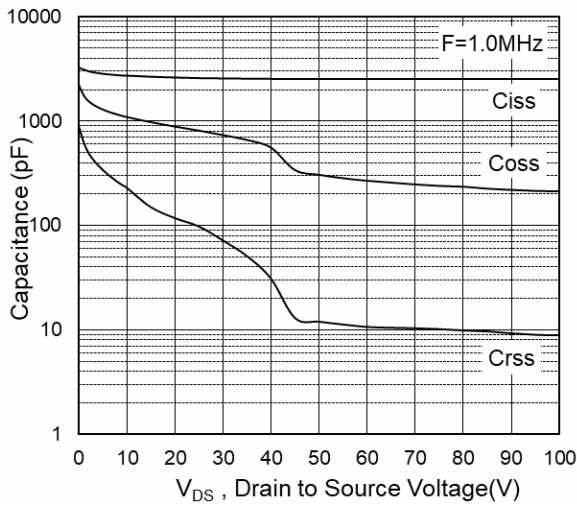


Fig.7 Capacitance

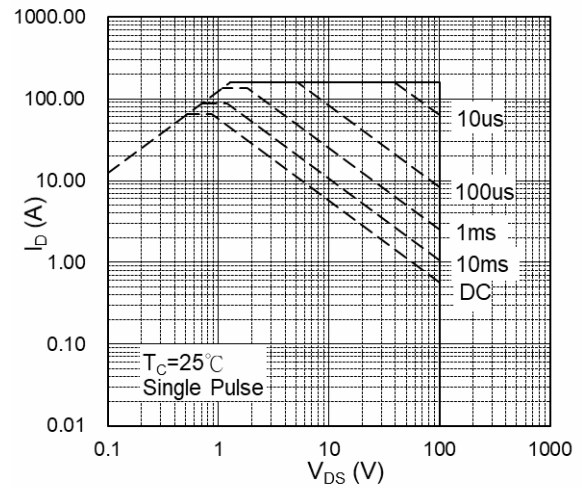


Fig.8 Safe Operating Area

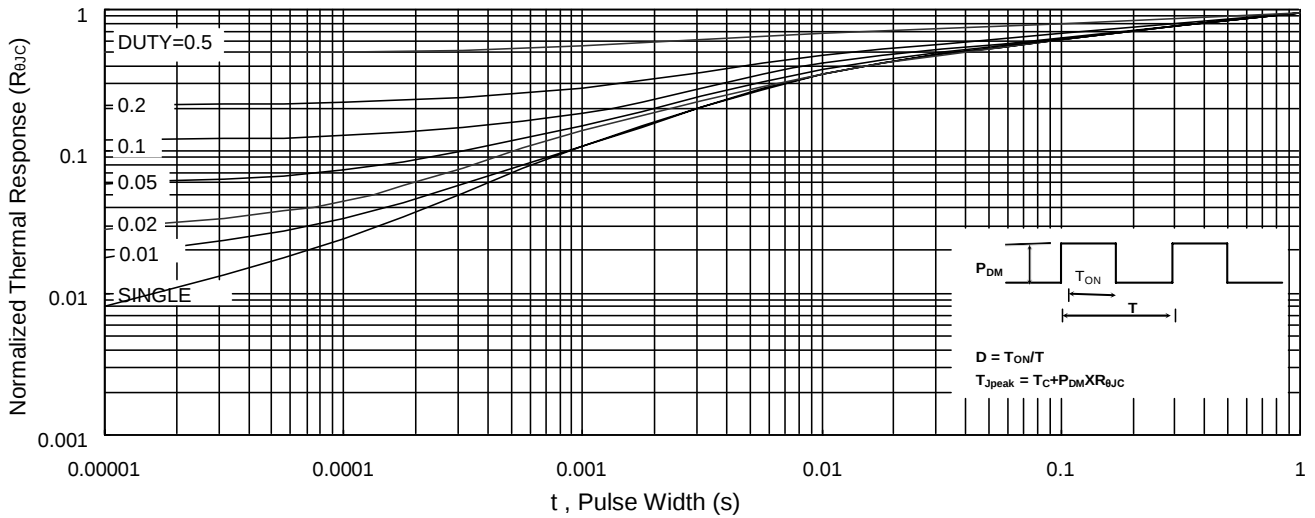


Fig.9 Normalized Maximum Transient Thermal Impedance

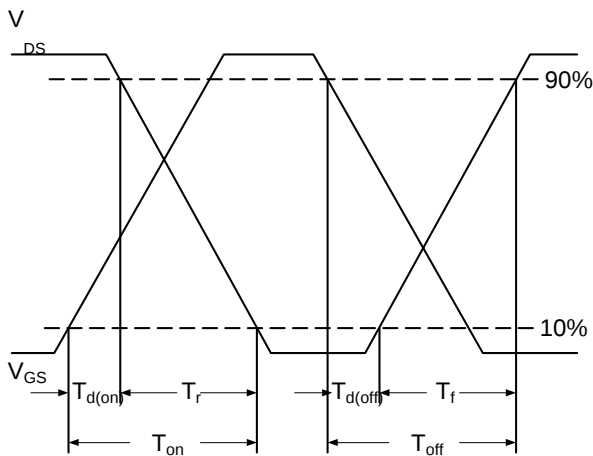


Fig.10 Switching Time Waveform

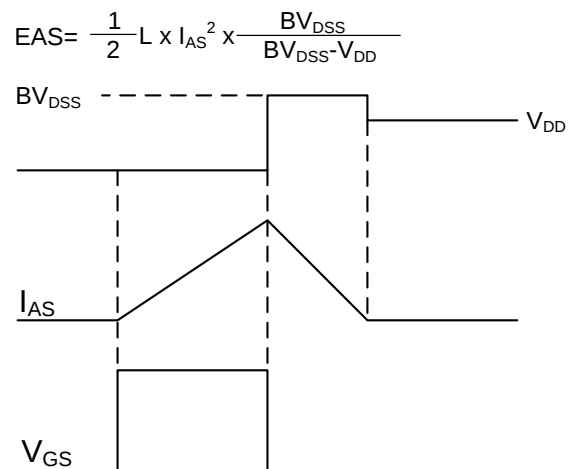


Fig.11 Unclamped Inductive Switching Waveform